SIEMENS

SFH615AA/AGB

5.3 kV TRIOS® OPTOCOUPLER
HIGH RELIABILITY

FEATURES

- **High Current Transfer Ratios**
  at 5 mA: 50–600%
  at 1 mA: 60% typical (>13)
- **Low CTR Degradation**
- **Good CTR Linearity Depending on Forward Current**
- **Isolation Test Voltage, 5300 VAC_{RMS}**
- **High Collector-Emitter Voltage, V_{CEO}=70 V**
- **Low Saturation Voltage**
- **Fast Switching Times**
- **Field-Effect Stable by TRIOS (TRansparent IOn Shield)**
- **Temperature Stable**
- **Low Coupling Capacitance**
- **End-Stackable, .100"(2.54 mm) Spacing**
- **High Common-Mode Interference Immunity (Unconnected Base)**
- **Underwriters Lab File #52744**
- **VDE 0884 Available with Option 1**
  SMD Option – See SFH6106/16/56 Data Sheet

DESCRIPTION

The SFH615AA/AGB features a high current transfer ratio, low coupling capacitance and high isolation voltage. These couplers have a GaAs infrared emitting diode emitter, which is optically coupled to a silicon planar phototransistor detector, and is incorporated in a plastic DIP-4 package.

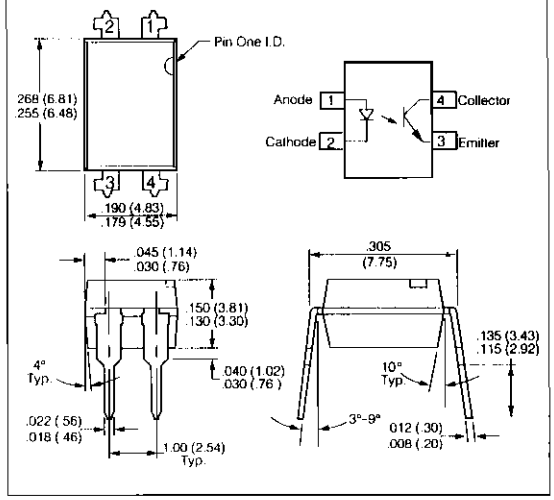
The coupling devices are designed for signal transmission between two electrically separated circuits.

The couplers are end-stackable with 2.54 mm spacing.

Creepage and clearance distances of >8 mm are achieved with option 6. This version complies with IEC 950 (DIN VDE 0805) for reinforced insulation up to an operation voltage of 400 V_{RMS} or DC.

Specifications subject to change.

Package Dimensions in Inches (mm)



Maximum Ratings

Emitter

Reverse Voltage ..... 6 V
DC Forward Current ..... 60 mA
Surge Forward Current (t_P≤10 µs) ..... 2.5 A
Total Power Dissipation ..... 100 mW

Detector

Collector-Emitter Voltage ..... 70 V
Emitter-Collector Voltage ..... 7 V
Collector Current ..... 50 mA
Collector Current (t_P≤1 ms) ..... 100 mA
Total Power Dissipation ..... 150 mW

Package

Isolation Test Voltage between Emitter and Detector, refer to Climate DIN 40046, part 2, Nov. 74 ..... 5300 VAC_{RMS}
Creepage ..... ≥7 mm
Clearance ..... ≥7 mm
Insulation Thickness between Emitter and Detector ... ≥0.4 mm
Comparative Tracking Index per DIN IEC 112/VDE0 303, part 1 ..... ≥175
Isolation Resistance
V_{IO}=500 V, T_A=25°C ..... ≥10^{12} Ω
V_{IO}=500 V, T_A=100°C ..... ≥10^{11} Ω
Storage Temperature Range ..... –55 to +150°C
Ambient Temperature Range ..... –55 to +100°C
Junction Temperature ..... 100°C
Soldering Temperature (max. 10 s. Dip Soldering Distance to Seating Plane ≥1.5 mm) ..... 260°C

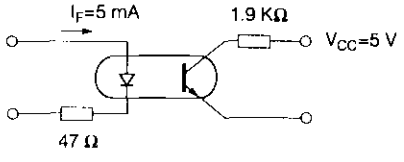
Characteristics (T_A=25°C)

Description	Symbol		Unit	Condition
Emitter (IR GaAs)				
Forward Voltage	V_F	1.25 (≤1.65)	V	I_F=60 mA
Reverse Current	I_R	0.01 (≤10)	µA	V_R=6 V
Capacitance	C_0	13	pF	V_R=0 V, f=1 MHz
Thermal Resistance	R_{thJA}	750	K/W	
Detector (Si Phototransistor)				
Capacitance	C_{CE}	5.2	pF	V_{CE}=5 V, f=1 MHz
Thermal Resistance	R_{thJA}	500	K/W	
Package				
Collector-Emitter Saturation Voltage	V_{CESAT}	0.25 (≤0.4)	V	I_F=10 mA, I_C=2.5 mA
Coupling Capacitance	C_C	0.4	pF	

Current Transfer Ratio (I_C/I_F at V_{CE}=5 V) **and Collector-Emitter Leakage Current**

Description	AA	AGB	
I_C/I_F (I_F=5 mA)	50–600	100–600	%
Collector-Emitter Leakage Current, I_{CEO} V_{CE}=10 V	10 (≤100)	10 (≤100)	nA

Switching Operation (with saturation)



		I_F=5 mA	
Turn-on Time	t_{ON}	2.0	µs
Turn-off Time	t_{OFF}	25	µs

Figure 1. Current transfer ratio (typ.) vs. temperature
I_F=10 mA, V_{CE}=0.5 V

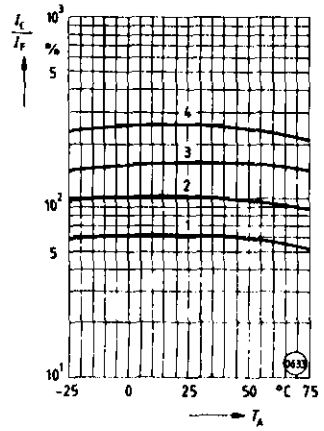


Figure 2. Output characteristics (typ.) Collector current vs. collector-emitter voltage T_A=25°C

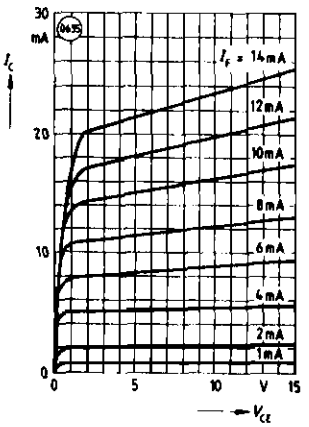


Figure 3. Diode forward voltage (typ.) vs. forward current

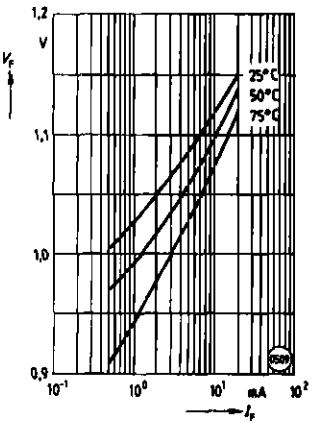


Figure 4. Transistor capacitance (typ.) vs. collector-emitter voltage
T_A=25°C, f=1 MHz

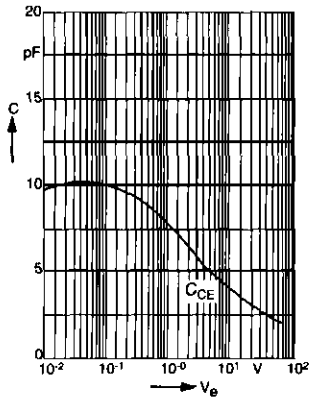


Figure 5. Permissiable pulse handling capability. Fwd. current vs. pulse width Pulse cycle D=parameter, T_A=25°C

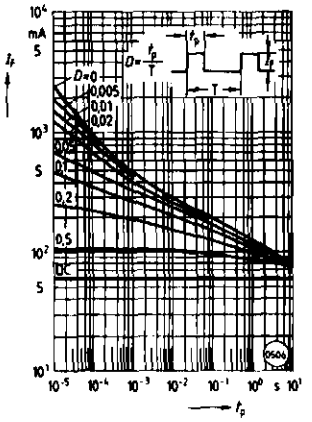


Figure 6. Permissible power dissipation vs. ambient temp.

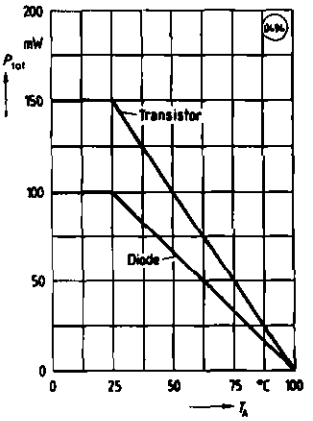


Figure 7. Permissible diode forward current vs. ambient temp.